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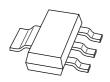
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# **PBHV9040Z**

500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor Rev. 02 — 15 January 2009 Product data sh

Product data sheet

### **Product profile**

### 1.1 General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540Z.

#### 1.2 Features

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

### 1.3 Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol          | Parameter                      | Conditions   | Min | Тур | Max   | Unit |
|-----------------|--------------------------------|--|-----|-----|-------|------|
| $V_{CESM}$      | collector-emitter peak voltage | $V_{BE} = 0 V$                                     | -   | -   | -500  | V    |
| $V_{CEO}$       | collector-emitter voltage      | open base  | -   | -   | -400  | V    |
| I <sub>C</sub>  | collector current              |  | -   | -   | -0.25 | Α    |
| h <sub>FE</sub> | DC current gain                | $V_{CE} = -10 \text{ V};$ $I_{C} = -50 \text{ mA}$ | 100 | 200 | -     |      |



# 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 2. Pinning information

Table 2. Pinning

|     | 9           |                    |                |
|-----|-------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1   | base        |                    |                |
| 2   | collector   | 4                  | 2, 4           |
| 3   | emitter     |                    | 1—             |
| 4   | collector   |                    | .,             |
|     |             |                    | 3              |
|     |             |                    | sym028         |

# 3. Ordering information

Table 3. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description  | Version |
| PBHV9040Z   | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

# 4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBHV9040Z   | V9040Z       |

# 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

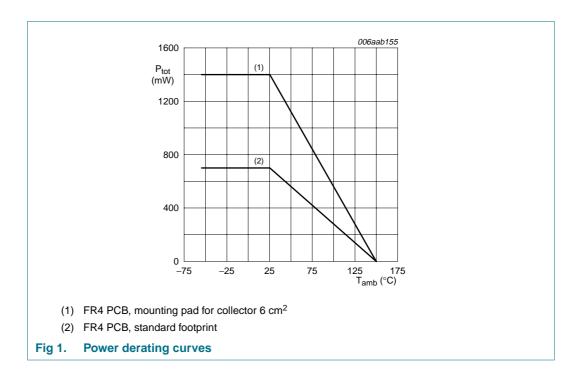
# 5. Limiting values

**Table 5.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

|                  |                                | 5 , (                                | ,           |       |      |
|------------------|--------------------------------|--------------------------------------|-------------|-------|------|
| Symbol           | Parameter                      | Conditions                           | Min         | Max   | Unit |
| $V_{CBO}$        | collector-base voltage         | open emitter                         | -           | -500  | V    |
| $V_{CEO}$        | collector-emitter voltage      | open base                            | -           | -400  | V    |
| $V_{CESM}$       | collector-emitter peak voltage | $V_{BE} = 0 V$                       | -           | -500  | V    |
| $V_{EBO}$        | emitter-base voltage           | open collector                       | -           | -6    | V    |
| I <sub>C</sub>   | collector current              |                                      | -           | -0.25 | Α    |
| I <sub>CM</sub>  | peak collector current         | single pulse; $t_p \le 1 \text{ ms}$ | -           | -0.5  | А    |
| I <sub>BM</sub>  | peak base current              | single pulse; $t_p \le 1 \text{ ms}$ | -           | -200  | mA   |
| P <sub>tot</sub> | total power dissipation        | $T_{amb} \le 25  ^{\circ}C$          | <u>[1]</u>  | 0.7   | W    |
|                  |                                |                                      | [2]         | 1.4   | W    |
| Tj               | junction temperature           |                                      | -           | 150   | °C   |
| T <sub>amb</sub> | ambient temperature            |                                      | <b>–</b> 55 | +150  | °C   |
| T <sub>stg</sub> | storage temperature            |                                      | -65         | +150  | °C   |
|                  |                                |                                      |             |       |      |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





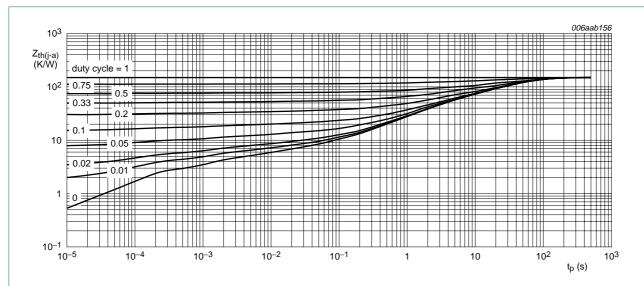
### 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

#### 6. Thermal characteristics

Table 6. Thermal characteristics

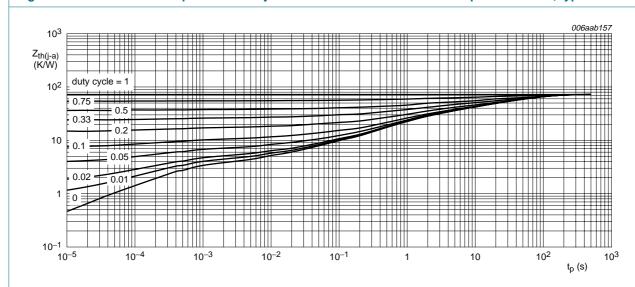
| Symbol         | Parameter  | Conditions  | Min          | Тур | Max | Unit |
|----------------|--|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | <u>[1]</u> _ | -   | 175 | K/W  |
|                |  |             | [2]          | -   | 89  | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -            | -   | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 7. Characteristics

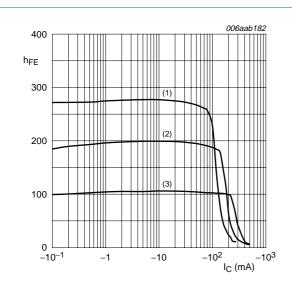
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

| Symbol             | Parameter                            | Conditions   | Min             | Тур       | Max  | Unit |
|--------------------|--------------------------------------|--|-----------------|-----------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off               | $V_{CB} = -320 \text{ V}; I_E = 0 \text{ A}$                                       | -               | -         | -100 | nA   |
|                    | current                              | $V_{CB} = -320 \text{ V; } I_{E} = 0 \text{ A;}$<br>$T_{j} = 150 ^{\circ}\text{C}$ | -               | -         | -10  | μΑ   |
| I <sub>CES</sub>   | collector-emitter<br>cut-off current | $V_{CE} = -320 \text{ V}; V_{BE} = 0 \text{ V}$                                    | -               | -         | -100 | nA   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | $V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}$   | -               | -         | -100 | nA   |
| h <sub>FE</sub>    | DC current gain                      | $V_{CE} = -10 \text{ V}$   |                 |           |      |      |
|                    |                                      | $I_C = -50 \text{ mA}$   | 100             | 200       | -    |      |
|                    |                                      | $I_C = -100 \text{ mA}$  | 80              | 200       | -    |      |
|                    |                                      | $I_C = -250 \text{ mA}$  | [ <u>1</u> ] 10 | 25        | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | $I_C = -100 \text{ mA}; I_B = -20 \text{ mA}$                                      | -               | -110      | -200 | mV   |
| $V_{BEsat}$        | base-emitter saturation voltage      | $I_C = -100 \text{ mA}; I_B = -20 \text{ mA}$                                      | [1] _           | <b>–1</b> | -1.1 | V    |
| f <sub>T</sub>     | transition frequency                 | $V_{CE} = -10 \text{ V}; I_E = -10 \text{ mA};$ f = 100 MHz                        | -               | 55        | -    | MHz  |
| C <sub>c</sub>     | collector capacitance                | $V_{CB} = -20 \text{ V}; I_E = i_e = 0 \text{ A};$<br>f = 1 MHz                    | -               | 7         | -    | pF   |
| C <sub>e</sub>     | emitter capacitance                  | $V_{EB} = -0.5 \text{ V}; I_C = I_c = 0 \text{ A};$<br>f = 1 MHz                   | -               | 150       | -    | pF   |
| t <sub>d</sub>     | delay time                           | $V_{CC} = -2 \text{ V}; I_C = -0.15 \text{ A};$                                    | -               | 9         | -    | ns   |
| t <sub>r</sub>     | rise time                            | $I_{Bon} = -0.03 \text{ A};$   | -               | 1810      | -    | ns   |
| t <sub>on</sub>    | turn-on time                         | $I_{Boff} = 0.03 A$  | -               | 1819      | -    | ns   |
| ts                 | storage time                         |  | -               | 715       | -    | ns   |
| t <sub>f</sub>     | fall time                            |  | -               | 1085      | -    | ns   |
| t <sub>off</sub>   | turn-off time                        |  | -               | 1800      | -    | ns   |

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

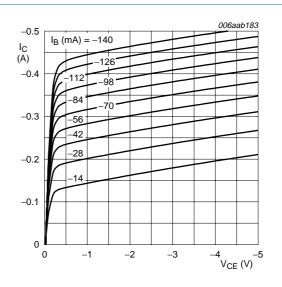




 $V_{CE} = -10 \text{ V}$ 

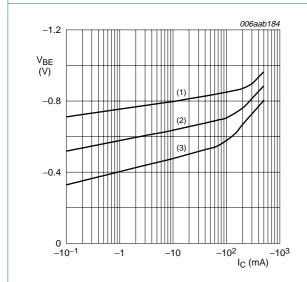
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \,^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

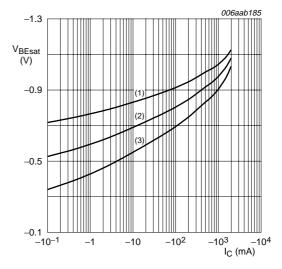
Fig 5. Collector current as a function of collector-emitter voltage; typical values





- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter voltage as a function of collector current; typical values



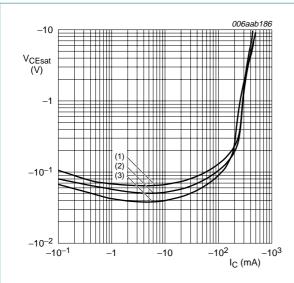
 $I_{\rm C}/I_{\rm B}=5$ 

- (1)  $T_{amb} = -55$  °C
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values

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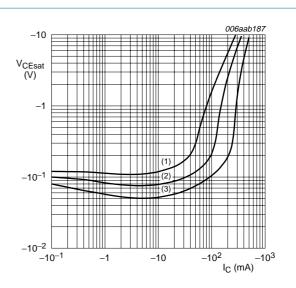
$$I_{\rm C}/I_{\rm B} = 5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values

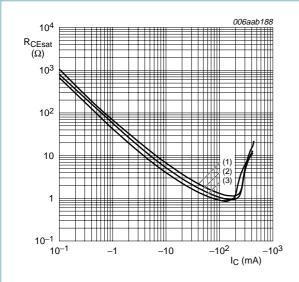


(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



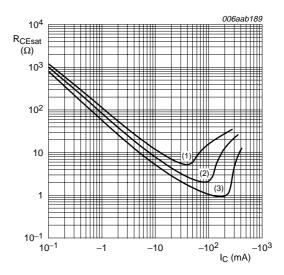
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

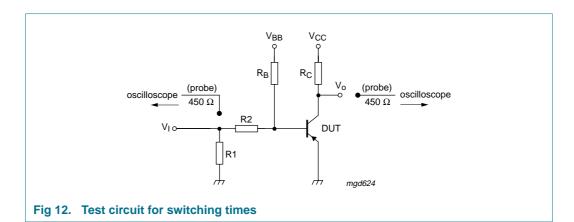
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values

500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

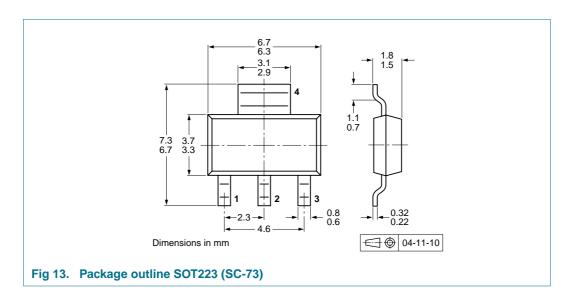
### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

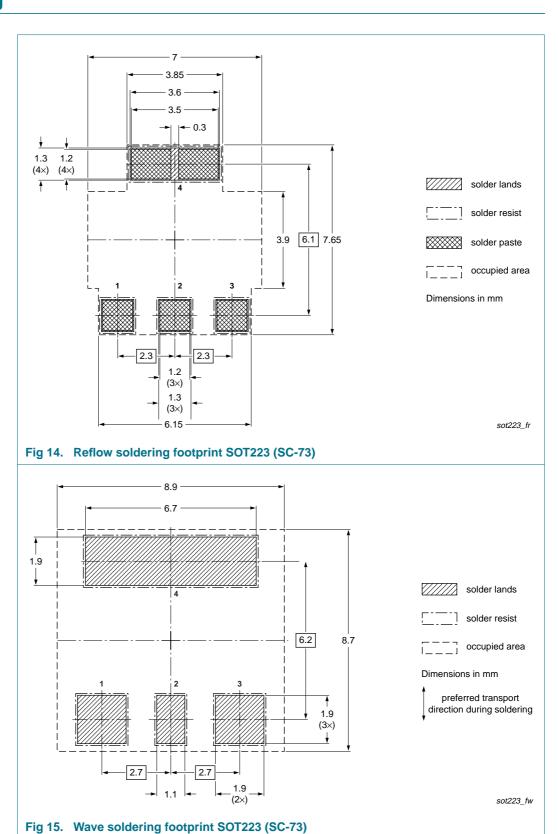
| Type number Package D |        | Description                     | Packing q | Packing quantity |  |
|-----------------------|--------|---------------------------------|-----------|------------------|--|
|                       |        |                                 | 1000      | 4000             |  |
| PBHV9040Z             | SOT223 | 8 mm pitch, 12 mm tape and reel | -115      | -135             |  |

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

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# 11. Soldering





500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

### Table 9. Revision history

| Document ID    | Release date    | Data sheet status  | Change notice | Supersedes  |
|----------------|-----------------|--|---------------|-------------|
| PBHV9040Z_2    | 20090115        | Product data sheet   | -             | PBHV9040Z_1 |
| Modifications: | • Table 7: toff | value changed from -100 value amended to 1800 ns<br>"Legal information": updated |               |             |
| PBHV9040Z_1    | 20080219        | Product data sheet   | -             | -           |

### 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### 500 V, 0.25 A PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

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